

# Amol Domaji Gaidhane

## List of Publications by Year in descending order

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11  
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1307594

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188  
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#	ARTICLE	IF	CITATIONS
1	Negative Capacitance Transistor to Address the Fundamental Limitations in Technology Scaling: Processor Performance. IEEE Access, 2018, 6, 52754-52765.	4.2	70
2	Compact Modeling of Drain Current, Charges, and Capacitances in Long-Channel Gate-All-Around Negative Capacitance MFIS Transistor. IEEE Transactions on Electron Devices, 2018, 65, 2024-2032.	3.0	61
3	Impact of Variability on Processor Performance in Negative Capacitance FinFET Technology. IEEE Transactions on Circuits and Systems I: Regular Papers, 2020, 67, 3127-3137.	5.4	44
4	Unveiling the Impact of IR-Drop on Performance Gain in NCFET-Based Processors. IEEE Transactions on Electron Devices, 2019, 66, 3215-3223.	3.0	30
5	Gate-Induced Drain Leakage in Negative Capacitance FinFETs. IEEE Transactions on Electron Devices, 2020, 67, 802-809.	3.0	22
6	Compact Modeling of Surface Potential, Drain Current and Terminal Charges in Negative Capacitance Nanosheet FET including Quasi-Ballistic Transport. IEEE Journal of the Electron Devices Society, 2020, 8, 1168-1176.	2.1	11
7	Modeling of Inner Fringing Charges and Short Channel Effects in Negative Capacitance MFIS Transistor. , 2019, , .		7
8	Ferroelectric FET-Based Implementation of FitzHugh-Nagumo Neuron Model. IEEE Transactions on Computer-Aided Design of Integrated Circuits and Systems, 2022, 41, 2107-2114.	2.7	7
9	Compact Modeling of Drain Current in Double Gate Negative Capacitance MFIS Transistor. , 2018, , .		6
10	Study of multi-domain switching dynamics in negative capacitance FET using SPICE model. Microelectronics Journal, 2021, 115, 105186.	2.0	6
11	Assessing Negative-Capacitance Drain-Extended Technology for High-Voltage Switching and Analog Applications. IEEE Transactions on Electron Devices, 2021, 68, 679-687.	3.0	4